

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for forming a silicon film, comprising:
providing an ink composition comprising a silicon compound onto a substrate by an ink jet process, wherein

the silicon compound is represented by Si_nX_m , Si_nX_{2n} or $\text{Si}_n\text{X}_{2n-2}$, n representing an integer of 3 or more, m representing an integer of n , $2n-2$, $2n$, or $2n+2$, and X representing a hydrogen atom and/or a halogen atom, and

evaporating a solvent of the ink composition to be provided onto the substrate has a surface tension of 20 to 70 dyn/cm for preventing non-linear flight of ink when emitted, and for retaining a stable meniscus shape in an ink jet nozzle form the silicon film, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight so that a uniform coating film is obtained.

2. (Previously Presented) The method for forming a silicon film according to claim 1, the ink composition being applied in an inert atmosphere.

3. (Currently Amended) The method for forming a silicon film according to claim 1, further comprising: ~~a drying step of removing a solvent of the composition; and~~
a step of pyrolyzing and/or photolyzing in the coating film.

4. (Previously Presented) The method for forming a silicon film according to claim 3, further comprising:

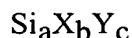
a step for irradiating the silicon film formed by heat treatment and/or light treatment with laser to convert the amorphous silicon film into a polycrystalline silicon film.

5. (Cancelled)

6. (Currently Amended) A method for forming a silicon film comprising:

applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process; and

evaporating a solvent of the composition to form the silicon film, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight so that a uniform coating film is obtained, wherein the silicon compound having at least one cyclic structure, the silicon compound is a silicon compound represented by:



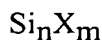
X representing a hydrogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to $2a+c$, and c representing an integer of 1 to a.

7. (Currently Amended) A method for forming a silicon film comprising:

applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process; and

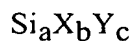
evaporating a solvent of the composition to form the silicon film, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight so that a uniform coating film is obtained,

the silicon compound having at least one cyclic structure, the silicon compound is a composition containing a silicon compound represented by the following general formula and a silicon compound represented by:



n representing an integer of 3 or more, m representing an integer of n, $2n-2$, or $2n$, and X representing a hydrogen atom and/or a halogen atom; and

silicon compound represented by:



X representing a hydrogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to $2a+c$, and c representing an integer of 1 to a, at least one of the compounds satisfying one of the formulae is cyclic.

8. (Previously Presented) The method for forming a silicon film according to claim 1, n being in a range of 5 to 20.

9. (Previously Presented) The method for forming a silicon film according to claim 6, $a+c$ being in a range of 5 to 20.

10. (Previously Presented) The method for forming a silicon film according to claim 1, the silicon compound being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.

11. (Previously Presented) The method for forming a silicon film according to claim 10, the solvent being a hydrocarbon solvent.

12. (Cancelled)

13. (Previously Presented) The method for forming a silicon film according to claim 1, the composition having a viscosity of 1 to 50 mPa·s.

14-23. (Cancelled)

24. (New) The method for forming a silicon film according to claim 1, the ink composition to be provided onto the substrate having a surface tension of 20 to 70 dyn/cm to prevent non-linear flight of ink when emitted, and to retain a stable meniscus shape in an ink-jet nozzle.